

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
-20V	14mΩ@-4.5V	-11A
	19mΩ@-2.5V	

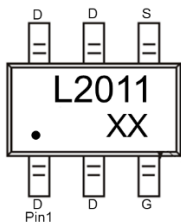
Feature

- Trench Power MOSFET
- Excellent $R_{DS(on)}$
- Low Gate Charge

Application

- Load Switch
- Battery Protection

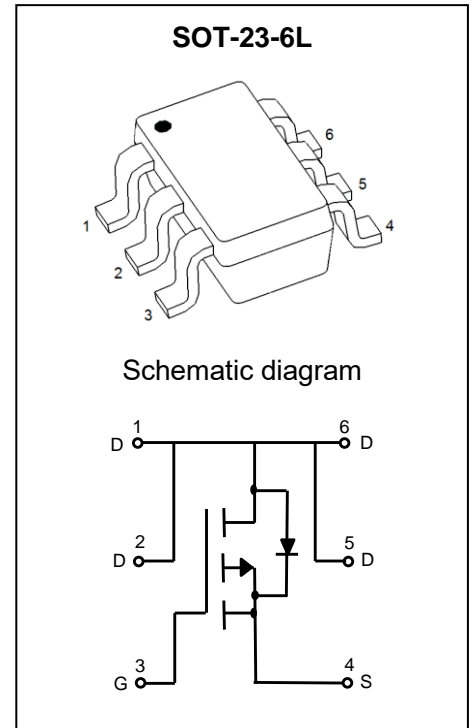
MARKING:



L2011 = Device Code

XX = Date Code

Solid Dot = Pin1



ABSOLUTE MAXIMUM RATINGS ($T_a=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	±12	V
Continuous Drain Current	I_D	-11	A
Plused Drain Current ⁽¹⁾	I_{DM}	-44	A
Power Dissipation ⁽²⁾	P_D	0.35	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	357	$^{\circ}C/W$
Junction Temperature	T_J	150	$^{\circ}C$
Storage Temperature	T_{STG}	-55~ +150	$^{\circ}C$

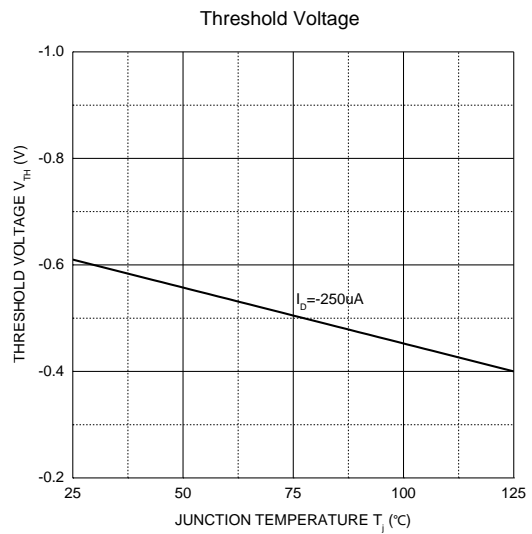
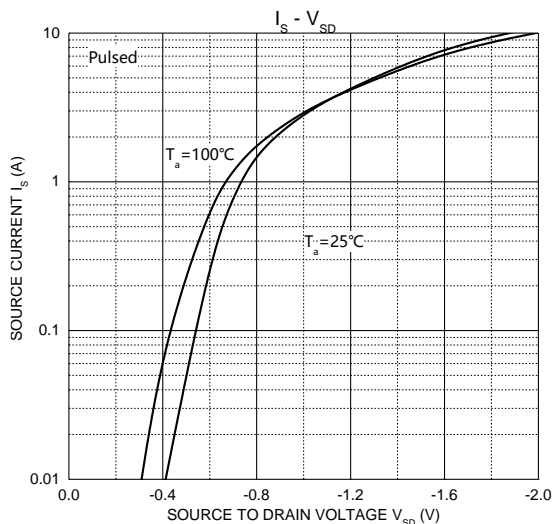
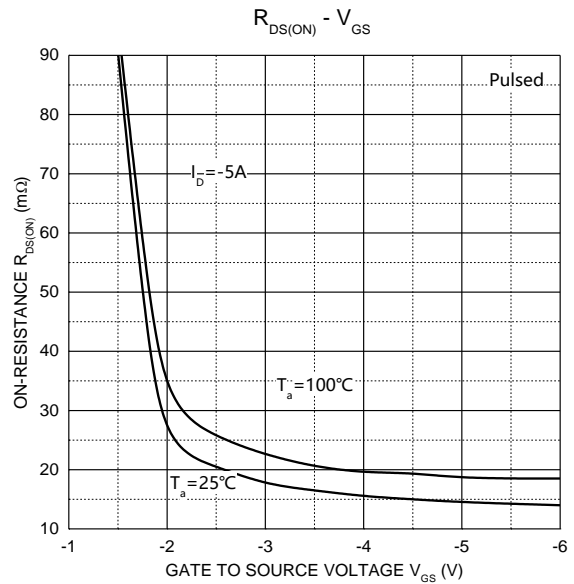
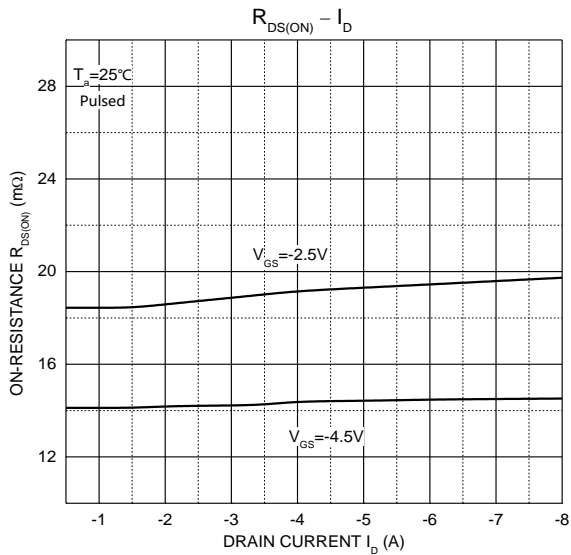
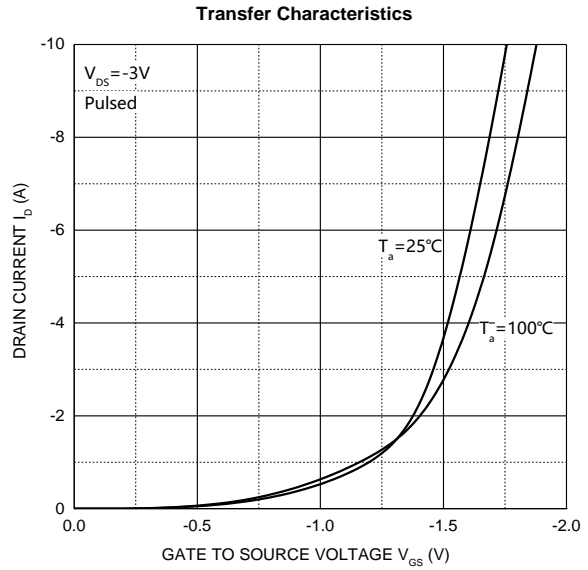
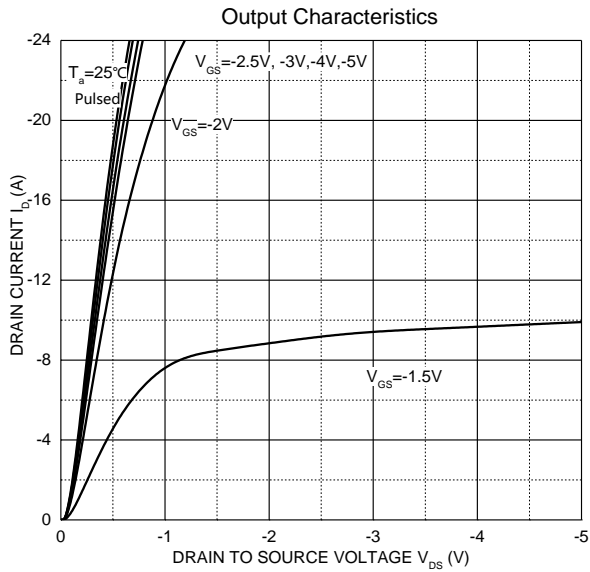
MOSFET ELECTRICAL CHARACTERISTICS(T_a=25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = -250μA	-20			V
Zero gate voltage drain current	I _{DSS}	V _{DS} = -16V, V _{GS} = 0V			-1	μA
Gate-body leakage current	I _{GSS}	V _{GS} = ±12V, V _{DS} = 0V			±100	nA
On Characteristics⁽³⁾						
Gate threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250μA	-0.4	-0.6	-1.0	V
Drain-source on-resistance	R _{DS(on)}	V _{GS} = -4.5V, I _D = -7.0A		14	18	mΩ
		V _{GS} = -2.5V, I _D = -6.0A		19	27	
Forward tranconductance	g _{FS}	V _{DS} = -10V, I _D = -7A	10			S
Dynamic characteristics						
Input Capacitance	C _{iss}	V _{DS} = -6V, V _{GS} = 0V, f = 1MHz		1900		pF
Output Capacitance	C _{oss}			390		
Reverse Transfer Capacitance	C _{rss}			380		
Total Gate Charge	Q _g	V _{DS} = -6V, V _{GS} = -4.5V, I _D = -10A		35		nC
Gate-Source Charge	Q _{gs}			5		
Gate-Drain Charge	Q _{gd}			10		
SWITCHING CHARACTERISTICS						
Turn-on delay time	t _{d(on)}	V _{GEN} = -4.5V, V _{DD} = -10V, I _D = -1A, R _g = 10Ω		11		ns
Turn-on rise time	t _r			35		
Turn-off delay time	t _{d(off)}			30		
Turn-off fall time	t _f			10		
Drain-Source Diode Characteristics						
Diode Forward Current	I _S				-11	A
Diode Forward Voltage ⁽³⁾	V _{SD}	V _{GS} = 0V, I _{SD} = -1.9A			-1.2	V

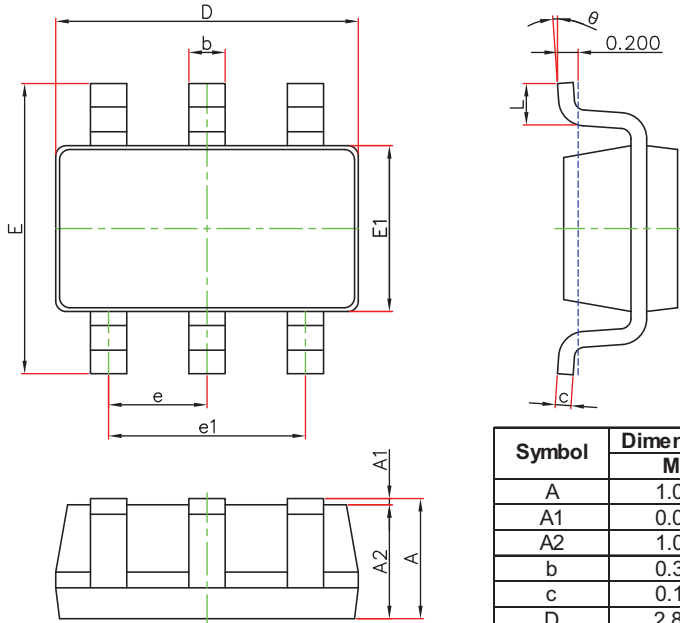
Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. This test is performed with no heat sink at T_a=25°C.
3. Pulse Test: Pulse With ≤300μs, Duty Cycle ≤2%.

Typical Electrical and Thermal Characteristics



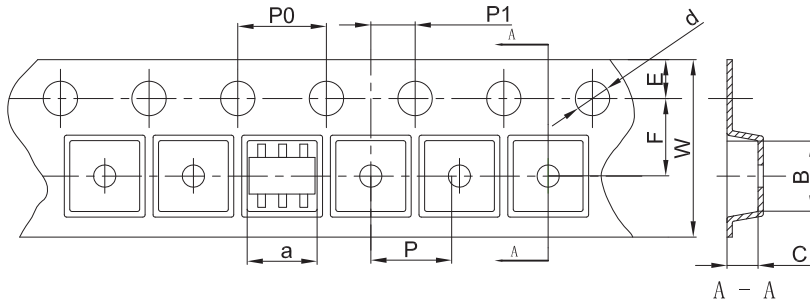
SOT-23-6L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

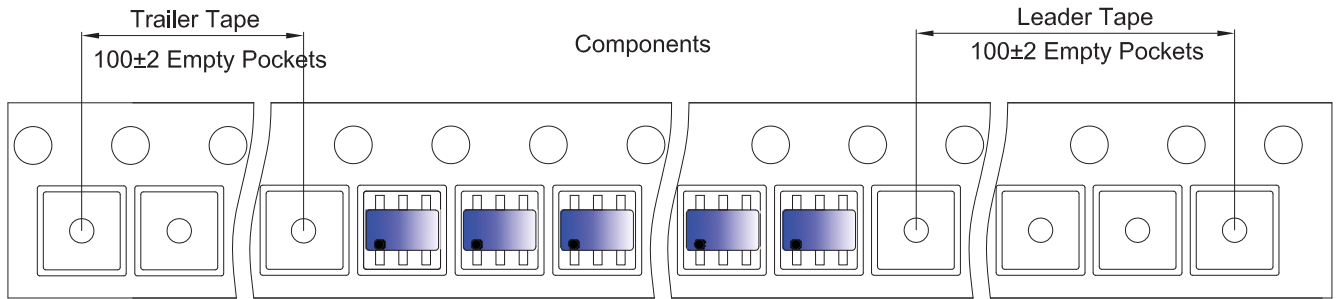
SOT-23-6L Tape and Reel

SOT-23-6L Tape and Reel

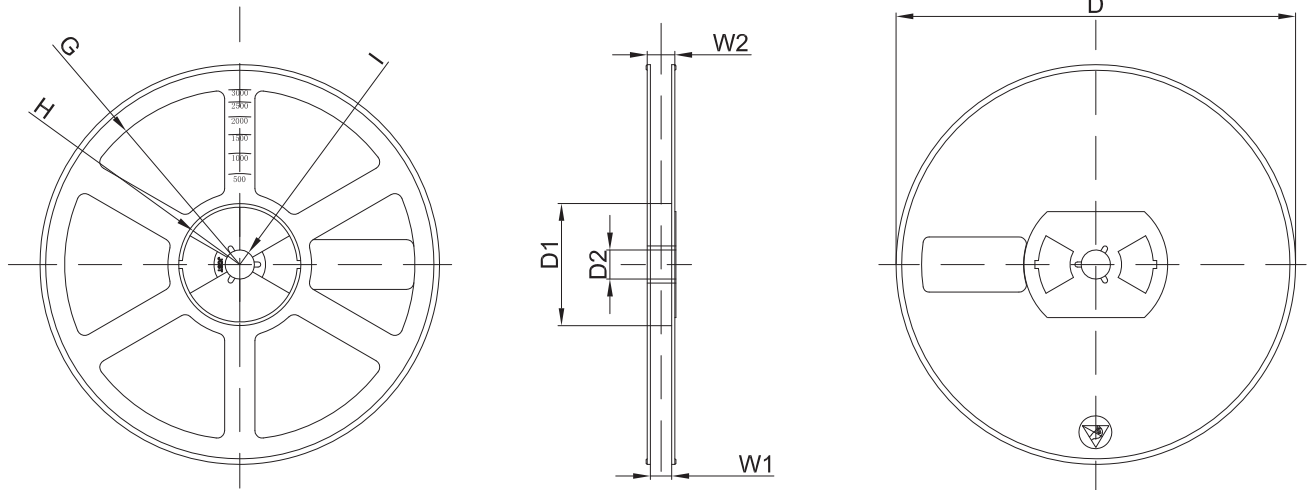


Dimensions are in millimeter										
Pkg type	a	B	C	d	E	F	P0	P	P1	W
SOT-23-6L	3.17	3.23	1.37	Ø1.55	1.75	3.50	4.00	4.00	2.00	8.00

SOT-23-6L Tape Leader and Trailer



SOT-23-6L Reel



Dimensions are in millimeter								
Reel Option	D	D1	D2	G	H	I	W1	W2
7" Dia	Ø180.00	60.00	13.00	R78.00	R25.60	R6.50	9.50	13.10

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
3000 pcs	7 inch	30,000 pcs	203×203×195	120,000 pcs	438×438×220	

单击下面可查看定价，库存，交付和生命周期等信息

[>>GP\(格瑞宝\)](#)